Electronic Supplementary Information for

Insights into charge carrier dynamics in organo-metal halide perovskites: from neat films to solar cells

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Sample	Method	Frequency (Hz)	light pulse (ns)	Time window or resolution	Light Intensity (mJ cm ⁻²)	Wavelength (nm)	μ (cm² V ⁻¹ s ⁻¹)	Carrier lifetime (μs)	Diffusion coefficient (cm ² s ⁻¹)	Diffusion length (µm)	Carrier concentration or trap density (cm ⁻³)	Conductivity $(\Omega^{-1} { m cm}^{-1})$	Ref.	
1-MΔPhI ₂ film	CELIV	2 5 x 10 ⁴	3_7		0.1	532	3 2 x 10 ^{−4}						ACS Appl. Mater. Interfaces,	
	CLLIV	2.5 ~ 10	5-7		0.1	552	5.2 ~ 10						2015, 7, 4471–4475	
1-MAPbl₂/PCBM bilaver	CELIV	2.5×10^4	3–7		0.1	532	7.1 × 10 ⁻⁴						ACS Appl. Mater. Interfaces,	
	02217	210 1 20	57		0.1	562	,11 10						2015, 7, 4471–4475	
2-MAPbl ₃ /PCBM bilaver	CELIV	2.5×10^4	3–7		0.1	532	5.29 ×						ACS Energy Lett., 2016, 1,	
	0111		•		0.1		10 ⁻⁴						1000-1006	
							0.67 ×							
MAPbl ₃ film	CELIV	2.5×10^{4}	3×10^{4}		< 5 × 10 ⁻⁵	473	10 ⁻³						Nano Energy, 2016, 27,	
							1.07 ×						569–576.	
							10 ⁻³							
HC 2D {(MA) _{n - 1} Pb _n I _{3n + 1} } ²⁻ film	Dark- CELIV	3.1×10^{4}					0.011						Nature, 2016, 536, 312–316	
2D {(MA) _{n - 1} Pb _n I _{3n + 1} } ²⁻ film	Dark- CELIV	3.1×10^{4}					0.0015						Nature, 2016, 536, 312–316	
MADH	CEUM	2.5×10^{4}	Л		0 062_2 47	522	10-4_10-3						Adv. Energy Mater. 2017,	
IVIAF DI3	CLLIV	1.0×10^{4}	1.0×10^{4}	4		0.002-2.47	552	10 -10						1602610
1 MADDL /DCRM bilayor	TOF	10	2 7		0 1	522	5.4×10^{-4}						ACS Appl. Mater. Interfaces,	
	IOP	10	5-7		0.1	552	4.5×10^{-4}						2015, 7, 4471–4475	
							8.65 ×							
2-MAPhla/PCBM hilaver	TOF	10	3_7		0.1	532	10 ⁻⁵						ACS Energy Lett., 2016, 1,	
	101	10	5-7		0.1	552	9.38 ×						1000-1006	
							10 ⁻⁵							
MAPbBr ₃ single crystals	TOF	200	5			355	115						Science, 2015, 347, 519–522	
MAPbl ₃ single crystals	TOF	> 100	4			337	24.0						Science, 2015, 347, 967–970	
							8.04 ×							
	тог	10	3–7		<u> </u>	522	10 ⁻⁵						Adv Sci 2016 2 1500422	
PDS-IVIAPDI3 CQDS	IOF	10			0.1	552	2.68 ×						Auv. Sci., 2010, 5, 1500452	
							10 ⁻⁵							
							9.91 ×							
DES MADEL /DES EDT CODE	TOF	10	3–7		0.1	522	10 ⁻⁵						Adv Sci 2016 2 1500/22	
	is IUF	10				725	1.04 ×						AUV. JUI., 2010, 3, 1300432	
								10 ⁻⁴						
ΜΔΡΗ	FFT						2.1×10^{-2}						Nat. Commun., 2015, 6,	
	FLI						7.2×10^{-2}						7383	

Table S1. Transport parameters calculated by various transient and steady-state measurements

CH_3NH_2 treated MAPbI ₃	FET	22.75	
MAPbl ₃ microplate crystals	FET	3 4	
MAPbBr ₃ single crystals	Hall	20–60	$5 \times 10^{9} - 5 \times 10^{10}$

MAPbI ₃ single crystals	Hall						105				9 × 10 ⁹
MAPbl ₃ single crystals	TPV or IS	Nan	4	1500 us	10-100 mWcm-2	337		82 or 95		175	
MASnI ₃ single crystals	Hall						200				9×10^{17}
MAPbl₃ film	Hall										4–10 × 10 ¹³
vapor- and solution-grown MAPbl₃ films	Hall						0.5	30		23	10 ¹⁵ -10 ¹⁶
MAPbBr ₃ single crystals	Hall						60	2700		650	10 ¹¹ –10 ¹²
MAPbBr ₃ single crystals	Hall						10 20				10 ⁹ -10 ¹²
MAPbl ₃ single crystals	SCLC						164 24.8				3.6×10^{10} 4.5×10^{10}
MAPbl ₃ polycrystalline films	SCLC										2.0 × 10 ¹⁵
MAPbBr₃ single crystals	SCLC						38				5.8 × 10 ⁹
MAPbl ₃ single crystals	SCLC						2.5				3.3×10^{10}
α -phase FAPbI ₃ single crystals	SCLC						4.4				6.2×10^{11}
MAPbBr ₃ ISC	SCLC and Hall effect						60				2 × 10 ¹¹
MAPbl ₃ thin film	TRPL	500	7	80 ns	0.025	532		0.010			
$MAPbl_xCl_{3-x} \text{ thin film}$	TRPL	??						> 0.100			
MAPbl₃ polycrystalline film MAPbl₃/PCBM MAPbl₃/ Spiro-OMeTAD	TRPL	1000	0.15 × 10 ⁻³		1.3 × 10 ^{−3}	600		4.5×10^{-3} 3.7×10^{-4} 6.4×10^{-4}	0.011 0.017	0.09 0.13	

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Science, 2013, 342, 344-347

MAPbl _x Cl _{3-x} film	TRPL	1 × 10 ⁶	6 × 10 ⁻³		6.5 × 10 ¹⁵ cm ⁻³		10 ⁻¹ -10 ⁻²	7 × 10 ⁻³	0.04–0.05 0.1–2.5	1
MAPbl ₃	TRPL	5×10^{4}	3×10^{-4}	20 ps	2×10^{-4}			0.14		
MAPbl ₃ polycrystalline films	TRPL	1×10^{6}	1.4×10^{-4}		$4 \times 10^{16} \text{ cm}^{-3}$	700		0.02–0.1		
MAPBI _x Cl _{1-x} film MAPBI ₃ film	TRPL	0.3–10 × 10 ⁶			0.03	507		0.2727 9.6 × 10 ⁻³	0.042, 0.054 0.017, 0.011	1.069, 1.213 0.129, 0.105
MAPbBr _{3-x} Cl _x films	TRPL	100K	1	400 ns	NAN	377		0.1– 0.446		
MAPbI _{3-x} Cl _x /PMMA Al ₂ O ₃ /MAPbI _{3-x} Cl _x /PMMA TiO ₂ /MAPbI _{3-x} Cl _x /PMMA TiO ₂ / MAPbI _{3-x} Cl _x / Spiro- OMeTAD	TRPL	NAN	0.1	300 ns	<0.1	635		0.35 0.02/0.32 0.004 0.002		
MAPbBr ₃ single crystals	TA + TRPL		0.7	ns–µs		355		0.041 0.375		3 17
MAPbl ₃ single crystals	TA + TRPL		0.8	ns–µs		633		0.022 1.032		2 8
MAPbl ₃ /PCBM MAPbl ₃ /Spiro-OMeTAD	ТА	1000	3.5 × 10 ⁻⁵		1.4 × 10 ⁻³	450		6 × 10 ⁻⁶ 8 × 10 ⁻⁶		
MAPbl₃ films	ТА	1000	0.13E-3	400 ps	0.019	377		97, 105, 313 × 10 ⁻⁶		
MAPbl ₃	ТА	5×10^{4}	0.3 × 10 ⁻³		2 × 10 ⁻⁴	1.8 eV		0.1–1 × 10 ⁻³		
$MAPBI_xCl_{1-x} \text{ film}$	ТА	1000	0.15E-3	2000 ps	0.0013	500		0.283 0.288		
MAPbl ₃ thin film	TA	1000	0.13×10^{-3}		8 × 10 ⁻³	387			0.05–0.08	
MAPbl₃ film	TRTS	5000	3.5 × 10⁻⁵		0.2×10^{-3} 0.121	800	35			
MAPbI ₃ embed in mesoporous Al ₂ O ₃	TRTS	1000	8 × 10 ⁻⁵		0.4/pluse	796	20 25			
MAPbl ₃ embed in mesoporous Al ₂ O ₃	TRTS	1100	1E-3	2500 ps	6E-3~0.32	550	11.6 8.1 8.2			
MAPbI₃ single crystal	TRTS	1000	1E-3	1000ps	0.08-0.14	400	800			

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1-MAPbl ₃ film and MAPbl ₃ in mesoporous Al ₂ O ₃ scaffolds	TRMC	8.45 × 10 ⁹	3		410	3	1		
2-MAPbl₃ film	TRMC	10	5–8		355	20 10			
MAPbl _x Cl _{3-x} films	TRMC	10		10 ⁹ to 10 ¹³ photons/cm ²	600	30		10	5×10^{14}
MAPbl₃ single crystal	TRMC	10	3.5	4×10^{12} photons/cm ²	405		15	> 50	

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